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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	
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Sheet	1	of	2	Attorney Docket Number	SC11814TP

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U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. [1]	U.S. Patent Document Number Code [2]	Kind (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US6,300,208B1		Talwar et al.	Oct.9,2001	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. [1]	Foreign Patent Document Office Code [3] [2]	Number [4]	Kind (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [6]
	AB		WO 00/13213		Somit Talwar	Mar.9,2000		

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
D	AC	Cheolmin Park et al., "50nm SOI CMOS Transistors with Ultra Shallow Junction using Laser Annealing and Pre-Amorphization Implantation",	
D	AD	Jung-Ho Lee et al., "Laser Thermal Annealed SSR well Prior to Epi-channel Growth (LASPE) for 70 nm nFETs", 2000 IEEE, IEDM 00-441, pgs. 18.4.1 – 18.4.4.	
D	AE	Ken-ichi Goto et al., "Ultra-Low Contact Resistance for Deca-nm MOSFETs by Laser Annealing", 1999 IEEE, IEDM-931-IEDM-933, pgs. 20.7.1 – 20.7.3.	
D	AF	Somit Talwar et al., "Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing", 1999 IEEE, pgs. 1171-1174.	
D	AG	A. Sato et al., "Determination of Solid Solubility Limit of In and Sb in Si using Bonded Silicon-On-Insulator (SOI) Substrate, Proc. IEEE 1995 Int. Conference on Microelectronic Test Structures, Vol. 8, March 1995, pgs. 259-260.	
D	AH	Bin Yu et al., "70nm MOSFET with Ultra-Shallow, Abrupt, and Super-Doped S/D Extension Implemented by Laser Thermal Process (LTP), 1999 IEEE, IEDM 99-509 – 99-512, pgs. 20.4.1 – 20.4.4.	

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